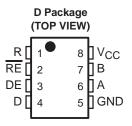
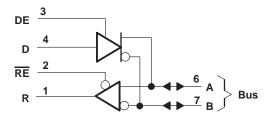
- **Controlled Baseline** 
  - One Assembly/Test Site, One Fabrication
- **Extended Temperature Performance of** -40°C to 125°C and -55°C to 125°C
- **Enhanced Diminishing Manufacturing** Sources (DMS) Support
- **Enhanced Product Change Notification**
- Qualification Pedigree†
- High-Speed Low-Power LinBiCMOS™ Circuitry Designed for Signaling Rates<sup>‡</sup> Up to 30 Mbps
- **Bus-Pin ESD Protection Exceeds 12-kV HBM**
- **Compatible With ANSI Standard** TIA/EIA-485-A and ISO 8482:1987(E)
- Low Skew
- **Designed for Multipoint Transmission on Long Bus Lines in Noisy Environments**
- **Low Disabled Supply Current** Requirements . . . 700 µA Maximum
- Common-Mode Voltage Range of -7 V to 12 V
- **Thermal-Shutdown Protection**
- **Driver Positive and Negative Current** Limiting
- Open-Circuit Fail-Safe Receiver Design
- Receiver Input Sensitivity . . . ±200 mV Max
- Receiver Input Hysteresis . . . 50 mV Typ
- Glitch-Free Power-Up and Power-Down **Protection**

† Component qualification in accordance with JEDEC and industry standards to ensure reliable operation over an extended temperature range. This includes, but is not limited to, Highly Accelerated Stress Test (HAST) or biased 85/85, temperature cycle, autoclave or unbiased HAST, electromigration, bond intermetallic life, and mold compound life. Such qualification testing should not be viewed as justifying use of this component beyond specified performance and environmental limits.

\$\frac{1}{2}\$ Signaling rate by TIA/EIA-485-A definition restrict transition times to 30% of the bit length, and much higher signaling rates may be achieved without this requirement as displayed in the TYPICAL CHARACTERISTICS of this device.



### logic diagram (positive logic)



#### **Function Tables**

#### **DRIVER**

INPUT	ENABLE	OUTPUTS		
D	DE	Α	В	
Н	Н	Н	L	
L	Н	L	Н	
X	L	Z	Z	
Open	Н	Н	L	

#### RECEIVER

DIFFERENTIAL INPUTS VA - VR	ENABLE RE	OUTPUT R
V <sub>ID</sub> ≥ 0.2 V	L	H
$-0.2 \text{ V} < \text{V}_{ID} < 0.2 \text{ V}$	Ĺ	?
V <sub>ID</sub> ≤ −0.2 V	L	L
x	Н	Z
Open	L	Н

H = high level,L = low level,? = indeterminate,

X = irrelevant.Z = high impedance (off)



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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#### description/ordering information

The SN65LBC176A-EP differential bus transceiver is a monolithic, integrated circuits designed for bidirectional data communication on multipoint bus-transmission lines. The SN65LBC176A-EP is designed for balanced transmission lines and is compatible with ANSI standard TIA/EIA-485-A and ISO 8482. The SN65LBC176A-EP offers improved switching performance over its predecessors without sacrificing significantly more power.

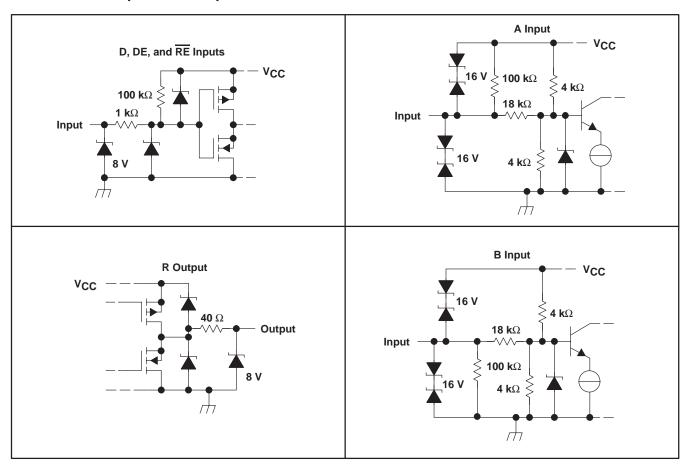
The SN65LBC176A-EP combines a 3-state, differential line driver and a differential input line receiver, both of which operate from a single 5-V power supply. The driver and receiver have active-high and active-low enables, respectively, which can externally connect together to function as a direction control. The driver differential outputs and the receiver differential inputs connect internally to form a differential input/output (I/O) bus port that is designed to offer minimum loading to the bus whenever the driver is disabled or V<sub>CC</sub> = 0. This port features wide positive and negative common-mode voltage ranges, making the device suitable for party-line applications. Low device supply current can be achieved by disabling the driver and the receiver.

#### ORDERING INFORMATION

TA	PACK	AGE†	ORDERABLE PART NUMBER	TOP-SIDE MARKING
-40°C to 125°C	SOIC - D	Tape and Reel	SN65LBC176AQDREP	176AEP
-55°C to 125°C	SOIC - D	Tape and Reel	SN65LBC176AMDREP	176MEP

<sup>†</sup>Package drawings, standard packing quantities, thermal data, symbolization, and PCB design quidelines are available at www.ti.com/sc/package.

#### schematics of inputs and outputs





### absolute maximum ratings†

Supply voltage, V <sub>CC</sub> (see Note 1)	0.3 V to 6 V
Voltage range at any bus terminal (A or B)	–10 V to 15 V
Input voltage, V <sub>I</sub> (D, DE, R, or RE)	$\dots$ -0.3 V to V <sub>CC</sub> + 0.5 V
Electrostatic discharge: Bus terminals and GND, Class 3, A: (see Note 2)	
Bus terminals and GND, Class 3, B: (see Note 2)	400 V
All terminals, Class 3, A:	4 kV
All terminals, Class 3, B:	400 V
Continuous total power dissipation (see Note 3)	See Dissipation Rating Table
Storage temperature range, T <sub>stq</sub> (see Note 4)	65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

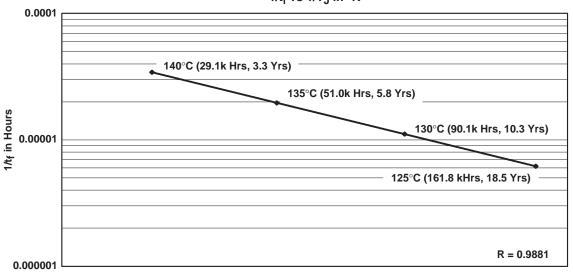
- NOTES: 1. All voltage values, except differential I/O bus voltage, are with respect to network ground terminal.
  - 2. The maximum operating junction temperature is internally limited. Use the dissipation rating table to operate below this temperature.
  - 3. Tested in accordance with MIL-STD-883C, Method 3015.7
  - 4. Long-term, high-temperature storage and/or extended use at maximum recommended operating conditions may result in a reduction of overall device life. See http://www.ti.com/ep\_quality for additional information on enhanced plastic packaging.

#### **DISSIPATION RATING TABLE**

PACKAGE	$T_{\mbox{A}} \le 25^{\circ}\mbox{C}$ POWER RATING	DERATING FACTOR‡ ABOVE T <sub>A</sub> = 25°C	T <sub>A</sub> = 70°C POWER RATING	T <sub>A</sub> = 85°C POWER RATING	T <sub>A</sub> = 125°C POWER RATING
D	725 mW	5.8 mW/°C	464 mW	377 mW	145 mW

<sup>&</sup>lt;sup>‡</sup> This is the inverse of the junction-to-ambient thermal resistance when the board is mounted and with no air flow.

# OPERATING LIFE DERATING TABLE – SN65LBC176AMDREP $1/t_{\rm f}$ vs $1/T_{\rm J}$ in $^{\circ}$ K



1/T<sub>J</sub> in °K

NOTES: A. See the data sheet for absolute maximum and maximum recommended operating conditions.

- B. Silicon operating life design goal is 10 years at 105°C junction temperature (does not include package interconnect life).
- C. Attached enhanced plastic product disclaimer applies.



# SN65LBC176A-EP **DIFFERENTIAL BUS TRANSCEIVER**

SGLS151C - DECEMBER 2002 - REVISED JULY 2004

#### recommended operating conditions

		MIN	NOM	MAX	UNIT
Supply voltage, V <sub>CC</sub>		4.75	5	5.25	V
Voltage at any hus terminal (separately or common mode			12	V	
Voltage at any bus terminal (separately or common mode	Voltage at any bus terminal (separately or common mode), V <sub>I</sub> or V <sub>IC</sub>				V
High-level input voltage, VIH (output recessive)	D, DE, and RE	2		Vcc	V
Low-level input voltage, V <sub>IL</sub> (output dominant)	D, DE, and RE	0		0.8	V
Differential input voltage, V <sub>ID</sub> (see Note 5)		-12§		12	V
	Driver	-60			
High-level output current, IOH	current, IOH Receiver				mA
Law book and and an extend to	Driver			60	4
Low-level output current, IOL	Receiver			8	mA
On another force shall be somewhat T	SN65LBC176AQ-EP	-40		125	00
Operating free-air temperature, T <sub>A</sub>	SN65LBC176AM-EP	-55		125	°C

<sup>§</sup> The algebraic convention, in which the least positive (most negative) limit is designated as minimum, is used in this data sheet. NOTE 5. Differential input/output bus voltage is measured at the noninverting terminal A with respect to the inverting terminal B.

# driver electrical characteristics over recommended operating conditions (unless otherwise noted)

	PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
VIK	Input clamp voltage	$I_{I} = -18 \text{ mA}$		-1.5	-0.8		V
		I <sub>O</sub> = 0		1.5	4	6	
VOD	Differential output voltage	$R_L = 54 \Omega$ ,	See Figure 1	0.9	1.5	6	V
		$V_{test} = -7 \text{ V to}$	12 V, See Figure 2	0.9	1.5	6	
Δ  V <sub>OD</sub>	Change in magnitude of differential output voltage	See Figure 1 ar	nd Figure 2	-0.2		0.2	V
V <sub>OC</sub> (SS)	Steady-state common-mode output voltage	See Figure 1	1.8	2.4	3	V	
Δ V <sub>OC</sub> (SS)	Change in steady-state common-mode output voltage†	See Figure 1	-0.2		0.2	V	
loz	High-impedance output current	See receiver input currents					
lіН	High-level enable input current	V <sub>I</sub> = 2 V		-100			μА
I <sub>IL</sub>	Low-level enable input current	V <sub>I</sub> = 0.8 V		-100			μА
los	Short-circuit output current	-7 V ≤ V <sub>O</sub> ≤ 12 V		-250	±70	250	mA
	_	V 0 V	Receiver disabled and driver enabled		5	9	
ICC	Supply current	$V_I = 0$ or $V_{CC}$ ,	Receiver disabled and driver disabled		0.4	0.7 mA	
			Receiver enabled and driver enabled		8.5	15	

<sup>†</sup> All typical values are at  $V_{CC} = 5 \text{ V}$ ,  $T_A = 25^{\circ}\text{C}$ .



SGLS151C - DECEMBER 2002 - REVISED JULY 2004

# driver switching characteristics over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP <sup>†</sup>	MAX	UNIT
t <sub>PLH</sub>	Propagation delay time, low-to-high level output		2		12	
tPHL	Propagation delay time, high-to-low level output	]	2		12	
		$R_L = 54 \Omega$ , $C_L = 50 pF$ , See Figure 3			2	ns
t <sub>r</sub>	Differential output signal rise time	See rigule 3			11	
tf	Differential output signal fall time		1.2		11	
<sup>t</sup> PZH	Propagation delay time, high-impedance to high-level output	$R_L$ = 110 Ω, See Figure 4			22	ns
tPZL	Propagation delay time, high-impedance to low-level output	$R_L$ = 110 Ω, See Figure 5			25	ns
tPHZ	Propagation delay time, high-level to high-impedance output	$R_L = 110 \Omega$ , See Figure 4			22	ns
tPLZ	Propagation delay time, low-level to high-impedance output	$R_L$ = 110 Ω, See Figure 5			22	ns

<sup>†</sup> All typical values are at  $V_{CC} = 5 \text{ V}$ ,  $T_A = 25^{\circ}\text{C}$ .

# receiver electrical characteristics over recommended operating conditions (unless otherwise noted)

	PARAMETER		TEST CONDIT	IONS	MIN	TYP <sup>†</sup>	MAX	UNIT
V <sub>IT+</sub>	Positive-going input threshold voltage	$I_O = -8 \text{ mA}$					0.2	V
VIT-	Negative-going input threshold voltage	I <sub>O</sub> = 8 mA						V
V <sub>hys</sub>	Hysteresis voltage (V <sub>IT+</sub> - V <sub>IT-</sub> )	Ŭ				50		mV
٧ıK	Enable-input clamp voltage	I <sub>I</sub> = –18 mA			-1.5	-0.8		V
Vон	High-level output voltage	$V_{ID} = 200 \text{ mV},$	$I_{OH} = -8 \text{ mA},$	See Figure 6	4	4.9		V
VOL	Low-level output voltage	$V_{ID} = 200 \text{ mV},$	$I_{OL} = 8 \text{ mA},$	See Figure 6		0.1	8.0	V
loz	High-impedance-state output current	$V_O = 0$ to $V_{CC}$			-10		10	μΑ
		V <sub>IH</sub> = 12 V,	V <sub>CC</sub> = 5 V			0.4	1	
	Bus land summed	V <sub>IH</sub> = 12 V,	VCC = 0	Other terror of OV		0.5	1	4
11	Bus input current	$V_{IH} = -7 V$ ,	V <sub>CC</sub> = 5 V	Other input at 0 V	-0.8	-0.4		mA
		$V_{IH} = -7 V$ ,	VCC = 0	]	-0.8	-0.3		
lн	High-level enable-input current	V <sub>IH</sub> = 2 V			-100			μΑ
IIL	Low-level enable-input current	V <sub>IL</sub> = 0.8 V			-100			μΑ
		.,,	Receiver enable	ed and driver disabled		4	7	
ICC	Supply current	V <sub>I</sub> = 0 or V <sub>CC</sub> , No load  Receiver disabled and driver disabled and driver ena		ed and driver disabled		0.4	0.7	mA
				ed and driver enabled		8.5	15	

<sup>&</sup>lt;sup>†</sup> All typical values are at  $V_{CC} = 5 \text{ V}$ ,  $T_A = 25^{\circ}\text{C}$ .



# SN65LBC176A-EP DIFFERENTIAL BUS TRANSCEIVER

SGLS151C - DECEMBER 2002 - REVISED JULY 2004

# receiver switching characteristics over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP†	MAX	UNIT
t <sub>PLH</sub>	Propagation delay time, output↑		7		30	ns
tPHL	Propagation delay time, output↓	V <sub>ID</sub> = −1.5 V to 1.5 V, See Figure 7	7		30	ns
t <sub>sk(p)</sub>	Pulse skew ( tpHL -tpLH )				6	ns
t <sub>r</sub>	Rise time, output	O			5	ns
t <sub>f</sub>	Fall time, output	See Figure 7			5	ns
tPZH	Output enable time to high level				50	ns
tPZL	Output enable time to low level	C <sub>I</sub> = 10 pF, See Figure 8			50	ns
t <sub>PHZ</sub>	Output disable time from high level	OL = 10 pr, See rigule o			60	ns
tPLZ	Output disable time from low level				40	ns

<sup>†</sup> All typical values are at  $V_{CC} = 5 \text{ V}$ ,  $T_A = 25^{\circ}\text{C}$ .



#### PARAMETER MEASUREMENT INFORMATION

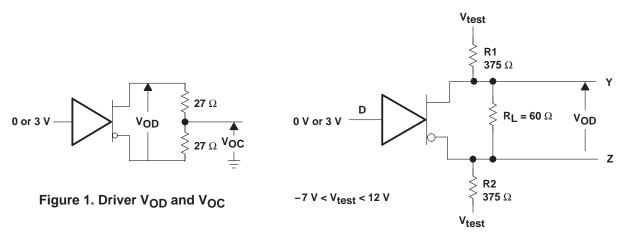
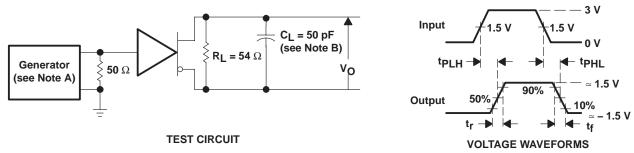
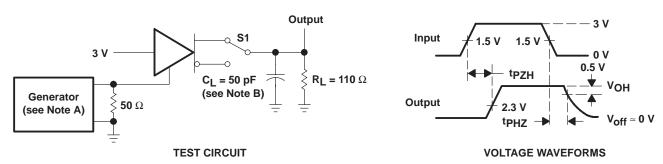


Figure 2. Driver V<sub>OD3</sub>



- NOTES: D. The input pulse is supplied by a generator having the following characteristics: PRR  $\leq$  1 MHz, 50% duty cycle,  $t_{\Gamma} \leq$  6 ns,  $t_{\Gamma} \leq$  7 ns,  $t_{\Gamma} \leq$  8 ns,  $t_{\Gamma} \leq$  8 ns,  $t_{\Gamma} \leq$  9 ns,  $t_$ 
  - E. C<sub>L</sub> includes probe and jig capacitance.

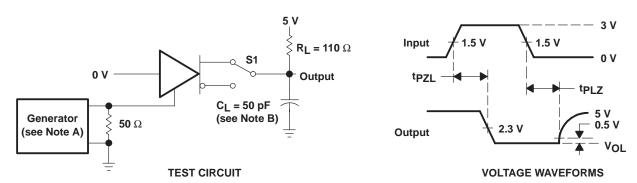
Figure 3. Driver Test Circuit and Voltage Waveforms



- NOTES: A. The input pulse is supplied by a generator having the following characteristics: PRR  $\leq$  1 MHz, 50% duty cycle,  $t_{\Gamma} \leq$  6 ns,  $t_{\Gamma} \leq$  7 ns,  $t_{\Gamma} \leq$  8 ns,  $t_{\Gamma} \leq$  9 ns,  $t_$ 
  - B. C<sub>L</sub> includes probe and jig capacitance.

Figure 4. Driver Test Circuit and Voltage Waveforms

#### PARAMETER MEASUREMENT INFORMATION



- NOTES: A. The input pulse is supplied by a generator having the following characteristics: PRR  $\leq$  1 MHz, 50% duty cycle,  $t_{\Gamma} \leq$  6 ns,  $t_{\Gamma} \leq$  7 ns,  $t_{\Gamma} \leq$  8 ns,  $t_{\Gamma} \leq$  8 ns,  $t_{\Gamma} \leq$  9 ns,  $t_$ 
  - B. C<sub>L</sub> includes probe and jig capacitance.

Figure 5. Driver Test Circuit and Voltage Waveforms

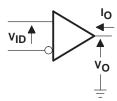
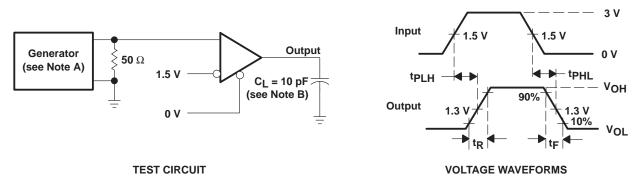


Figure 6. Receiver VOH and VOL

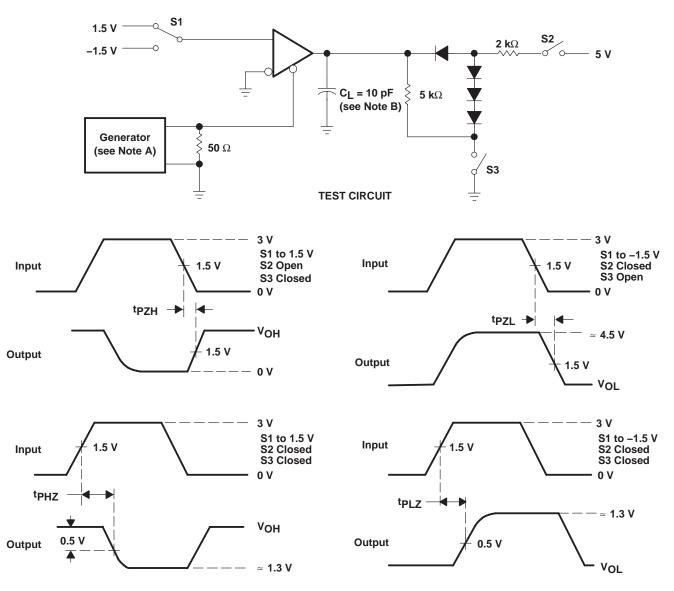


- NOTES: A. The input pulse is supplied by a generator having the following characteristics: PRR  $\leq$  1 MHz, 50% duty cycle,  $t_f \leq$  6 ns,  $t_f \leq$  8 ns,  $t_f \leq$  8 ns,  $t_f \leq$  9 ns,  $t_f$ 
  - B. C<sub>L</sub> includes probe and jig capacitance.

Figure 7. Receiver Test Circuit and Voltage Waveforms



#### PARAMETER MEASUREMENT INFORMATION



#### **VOLTAGE WAVEFORMS**

NOTES: A. The input pulse is supplied by a generator having the following characteristics: PRR  $\leq$  1 MHz, 50% duty cycle,  $t_{\Gamma} \leq$  6 ns,  $t_{\Gamma} \leq$  7 ns,  $t_{\Gamma} \leq$  8 ns,  $t_{\Gamma} \leq$  8 ns,  $t_{\Gamma} \leq$  9 ns,  $t_$ 

B. CL includes probe and jig capacitance.

Figure 8. Receiver Test Circuit and Voltage Waveforms

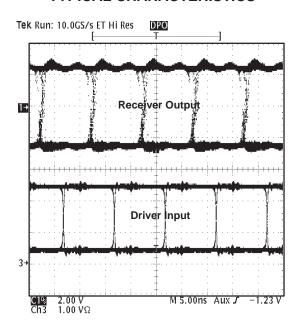




Figure 9. Typical Waveform of Non-Return-To-Zero (NRZ), Pseudorandom Binary Sequence (PRBS) Data at 100 Mbps Through 15m, of CAT 5 Unshielded Twisted Pair (UTP) Cable

TIA/EIA-485-A defines a maximum signaling rate as that in which the transition time of the voltage transition of a logic-state change remains less than or equal to 30% of the bit length. Transition times of greater length perform quite well, even though they do not meet the standard by definition.



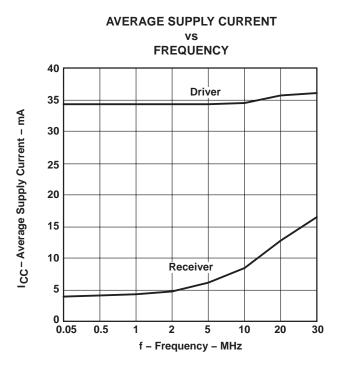


Figure 10

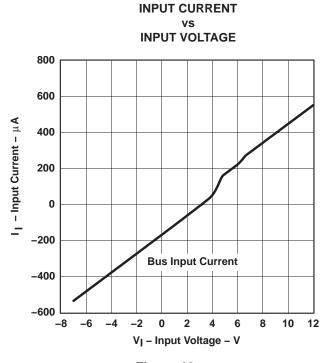


Figure 12

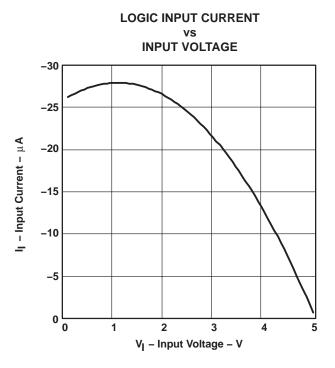


Figure 11

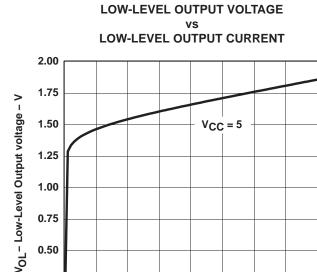


Figure 13

40

IOL - Low-Level Output Current - mA

50

60

70

80

0.75

0.50

0.25

0.00

10

20

30

# **DRIVER HIGH-LEVEL OUTPUT VOLTAGE HIGH-LEVEL OUTPUT CURRENT** 5 4.5 VOH - High-Level Output Voltage - V V<sub>CC</sub> = 5.25 V 3.5 3 2.5 $V_{CC} = 5 V$ 2 $V_{CC} = 4.75 V$ 1.5 0.5 -40 -50 -60 -30 I<sub>OH</sub> - High-Level Output Current - (mA)

#### Figure 14

# RECEIVER PROPAGATION TIME **CASE TEMPERATURE** 13.8 13.7 13.6 TPHL Receiver (ns) 13.5 13.4 13.3 13.2 13.1 13 12.9 \_40 25 70 Case Temperature - C Figure 16

# DRIVER DIFFERENTIAL OUTPUT VOLTAGE vs

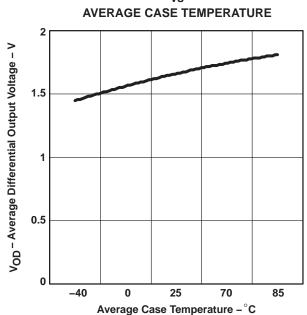


Figure 15

#### DRIVER PROPAGATION DELAY TIME

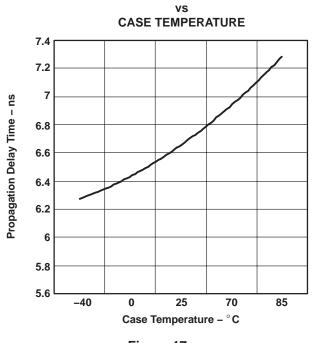


Figure 17

# DRIVER OUTPUT CURRENT vs SUPPLY VOLTAGE

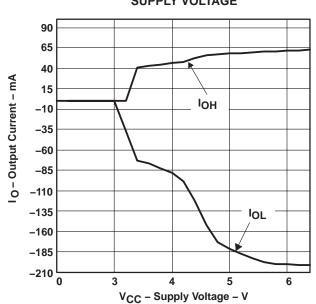


Figure 18





6-Feb-2020

#### **PACKAGING INFORMATION**

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN65LBC176AMDREP	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-55 to 125	176MEP	Samples
SN65LBC176AQDREP	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 125	176AEP	Samples
V62/03671-01XE	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 125	176AEP	Samples
V62/03671-02XE	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-55 to 125	176MEP	Samples

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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### PACKAGE OPTION ADDENDUM

6-Feb-2020

continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

#### OTHER QUALIFIED VERSIONS OF SN65LBC176A-EP:

■ Catalog: SN65LBC176A

NOTE: Qualified Version Definitions:

• Catalog - TI's standard catalog product

# PACKAGE MATERIALS INFORMATION

www.ti.com 12-Feb-2019

### TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65LBC176AMDREP	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
SN65LBC176AQDREP	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

# **PACKAGE MATERIALS INFORMATION**

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#### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65LBC176AMDREP	SOIC	D	8	2500	350.0	350.0	43.0
SN65LBC176AQDREP	SOIC	D	8	2500	350.0	350.0	43.0



SMALL OUTLINE INTEGRATED CIRCUIT



#### NOTES:

- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE INTEGRATED CIRCUIT



#### NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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